

A study of simulation and analysis in flash memory devices

鍾順泰、陳勝利

E-mail: 8700839@mail.dyu.edu.tw

ABSTRACT

In submicrometer flash memory devices, the almost injection models for programming operation is no more accurate to evaluate injection current. Therefor, we will present a novel model to simulate the charge injection in the flash momory. For erasing operation, a well-known model, F-N Electron Tunneling Model, will be used during theoretical simulation.

Keywords : 快閃記憶體

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